RoHS

COMPLIANT

HALOGEN

FREE

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Vishay Siliconix

N-Channel 20 V (D-S) MOSFET

Marking code: AD

Top View

PRODUCT SUMMARY									
V _{DS} (V)	20								
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 4.5 \text{ V}$	0.046								
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 2.5 \text{ V}$	0.063								
Q _g typ. (nC)	3.5								
I _D (A) ^a	6								
Configuration	Single								

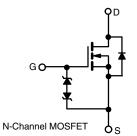
Bottom View

FEATURES

- TrenchFET® power MOSFET
- New thermally enhanced PowerPAK[®] SC-75 package
 - Small footprint area
 - Low on-resistance
- Typical ESD protection 560 V
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- Load switch for portable applications
- High frequency DC/DC converter



ORDERING INFORMATION						
Package	PowerPAK SC-75					
Lead (Pb)-free and halogen-free	SIB406EDK-T1-GE3					

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)								
PARAMETER		SYMBOL	LIMIT	UNIT				
Drain-source voltage		V_{DS}	20	V				
Gate-source voltage		V_{GS}	± 12	V				
	T _C = 25 °C		6 ^a					
Continuous drain current (T _{.1} = 150 °C)	T _C = 70 °C		6 ^a					
Continuous drain current (1 _J = 150 °C)	T _A = 25 °C	I _D	5.1 ^{b, c}					
	T _A = 70 °C		4.1 b, c	Α				
Pulsed drain current	•	I _{DM}	15					
Continuous source drain diada surrent	T _C = 25 °C		6 ^a					
Continuous source-drain diode current	T _A = 25 °C	- I _S	1.6 ^{b, c}					
	T _C = 25 °C		10					
Mandan and a substitution of the state of	T _C = 70 °C	<u> </u>	6.4	w				
Maximum power dissipation	T _A = 25 °C	P _D	1.95 ^{b, c}	VV				
	T _A = 70 °C		1.25 ^{b, c}					
Operating junction and storage temperature	T _J , T _{stg}	-55 to +150	°C					
Soldering recommendations (peak tempera	ture) ^{d, e}		260	-0				

THERMAL RESISTANCE RATINGS									
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT				
Maximum junction-to-ambient b, f	t ≤ 5 s	R _{thJA}	51	64	°C/W				
Maximum junction-to-case (drain)	Steady state	R_{thJC}	10	12.5	*C/W				

Notes

- a. Package limited
- b. Surface mounted on 1" x 1" FR4 board
- c. t = 5 s
- d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SC-75 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- f. Maximum under steady state conditions is 100 °C/W

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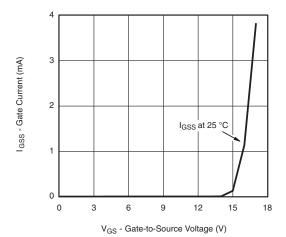
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static				•	•	
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	20	-	-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	L 050 A	-	23	-	1400
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA	-	-3.3	-	mV/°C
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_{D} = 250 \ \mu A$	0.6	-	1.4	V
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$	-	-	± 8	
Zana and a self-annual self-annual	I _{DSS}	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	-1	μA
Zero gate voltage drain current		V _{DS} = 20 V, V _{GS} = 0 V, T _J = 55 °C	-	-	-10	
On-state drain current a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	10	-	-	Α
Deline and the second	_	$V_{GS} = 4.5 \text{ V}, I_D = 3.9 \text{ A}$	-	0.037	0.046	
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 3.3 \text{ A}$	-	0.051	0.063	Ω
Forward transconductance a	9 _{fs}	$V_{DS} = 10 \text{ V}, I_D = 3.9 \text{ A}$	-	14	-	S
Dynamic ^b						
Input capacitance	C _{iss}		-	350	-	
Output capacitance	C _{oss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	63	-	pF
Reverse transfer capacitance	C _{rss}		-	37	-	
		$V_{DS} = 10 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 5.1 \text{ A}$	-	7.5	12	
Total gate charge	Q_g		-	3.5	5.5	
Gate-source charge	Q _{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 5.1 \text{ A}$	-	0.95	-	nC
Gate-drain charge	Q _{gd}		-	0.75	-	
Gate resistance	R_{g}	f = 1 MHz	-	3.5	-	Ω
Turn-on delay time	t _{d(on)}		-	10	15	
Rise time	t _r	V_{DD} = 10 V, R_L = 2.4 Ω	-	12	20	
Turn-off delay time	t _{d(off)}	$I_D \cong 4.1 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$	-	18	30	
Fall time	t _f		-	12	20	
Turn-on delay time	t _{d(on)}		-	5	10	ns
Rise time	t _r	V_{DD} = 10 V, R_L = 2.4 Ω	-	12	20	- - -
Turn-off delay time	t _{d(off)}	$I_D \cong 4.1 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	15	25	
Fall time	t _f		-	10	15	
Drain-Source Body Diode Characteristic	s		•	•	•	
Continuous source-drain diode current Is		T _C = 25 °C	-	-	6	
ulse diode forward current I _{SM}			-	-	15	A
Body diode voltage V _{SD}		I _S = 4.1 A, V _{GS} = 0 V	-	0.8	1.2	V
Body diode reverse recovery time	t _{rr}		-	15	30	ns
Body diode reverse recovery charge	Q _{rr}	I _F = 4.1 A, di/dt = 100 A/μs,	-	8	20	nC
Reverse recovery fall time	t _a	$T_J = 25 ^{\circ}\text{C}$	-	8	-	
Reverse recovery rise time	t _b		-	7	-	ns

Notes

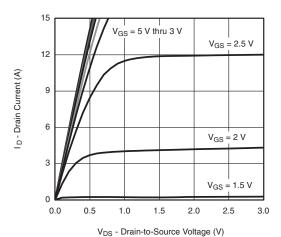
- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

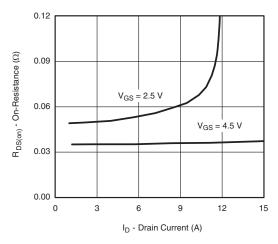




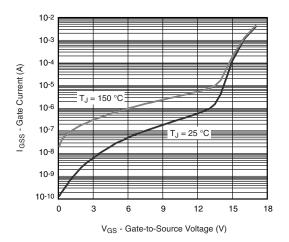
Gate Current vs. Gate-Source Voltage



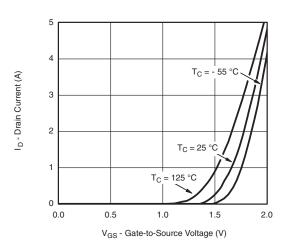
Output Characteristics



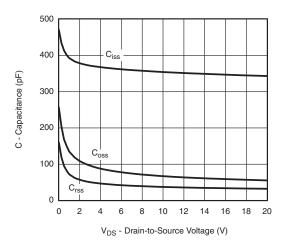
On-Resistance vs. Drain Current and Gate Voltage



Gate Current vs. Gate-Source Voltage

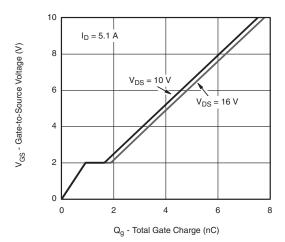


Transfer Characteristics

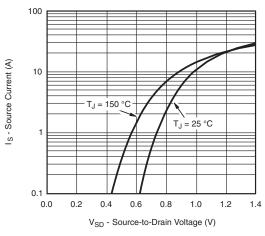


Capacitance

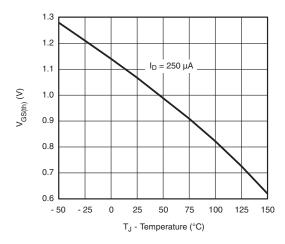




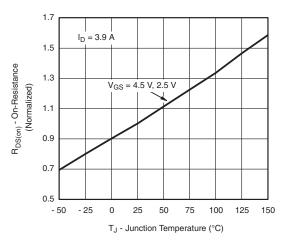
Gate Charge



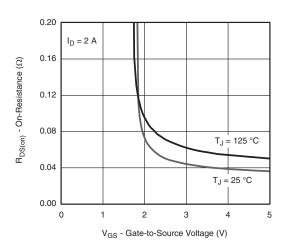
Source-Drain Diode Forward Voltage



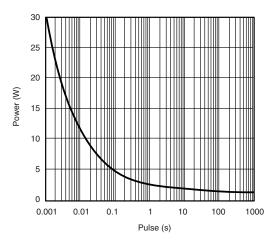
Threshold Voltage



On-Resistance vs. Junction Temperature

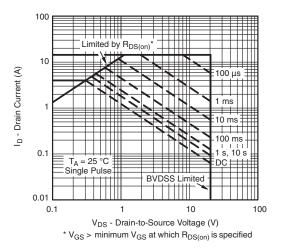


On-Resistance vs. Gate-to-Source Voltage

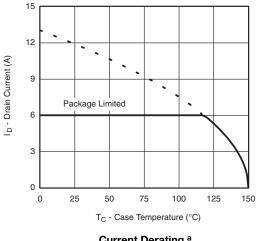


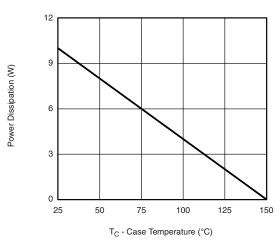
Single Pulse Power (Junction-to-Ambient)





Safe Operating Area, Junction-to-Ambient



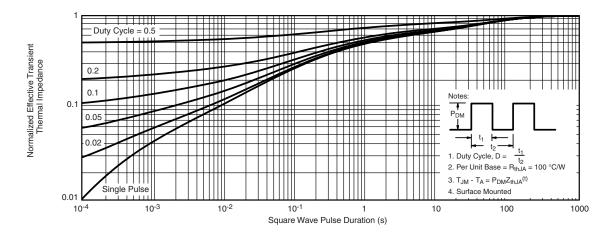


Current Derating a

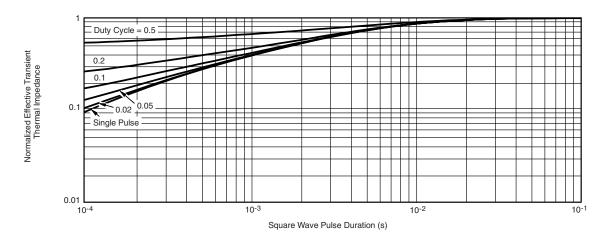
Power Derating

c. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit





Normalized Thermal Transient Impedance, Junction-to-Ambient



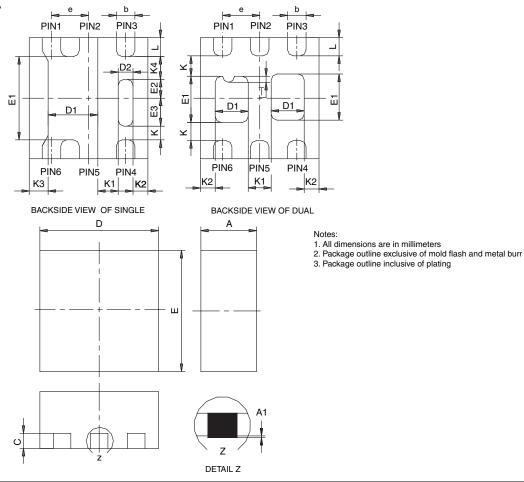
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?69088.





PowerPAK® SC75-6L



	SINGLE PAD						DUAL PAD					
DIM	M	ILLIMETER	RS		INCHES		M	MILLIMETERS			INCHES	
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A 1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.18	0.25	0.33	0.007	0.010	0.013	0.18	0.25	0.33	0.007	0.010	0.013
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067
D1	0.57	0.67	0.77	0.022	0.026	0.030	0.34	0.44	0.54	0.013	0.017	0.021
D2	0.10	0.20	0.30	0.004	0.008	0.012						1
E	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067
E1	1.00	1.10	1.20	0.039	0.043	0.047	0.51	0.61	0.71	0.020	0.024	0.028
E2	0.20	0.25	0.30	0.008	0.010	0.012						1
E3	0.32	0.37	0.42	0.013	0.015	0.017						1
е		0.50 BSC			0.020 BSC	;	0.50 BSC			0.020 BSC		
K		0.180 TYP			0.007 TYP)	0.245 TYP			0.010 TYP		
K 1		0.275 TYP 0.011 TYP			0.320 TYP			0.013 TYP				
K2	0.200 TYP 0.008 TYP			0.200 BSC			0.008 TYP					
К3		0.255 TYP 0.010 TYP										
K4	0.300 TYP			0.012 TYP								
L	0.15	0.25	0.35	0.006	0.010	0.014	0.15	0.25	0.35	0.006	0.010	0.014
Т							0.03	0.08	0.13	0.001	0.003	0.005
ECN: C-(17/31 Be	v C 06-Au	a-07		ı	ı	ı	1		ı	1	

ECN: C-07431 - Rev. C, 06-Aug-07

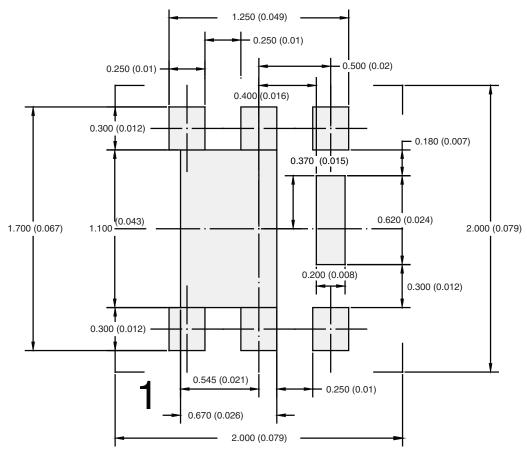
DWG: 5935

Document Number: 73000 06-Aug-07

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RECOMMENDED PAD LAYOUT FOR PowerPAK® SC75-6L Single



Dimensions in mm/(Inches)

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